

Silicon PNP Power Transistors

2SB887

DESCRIPTION

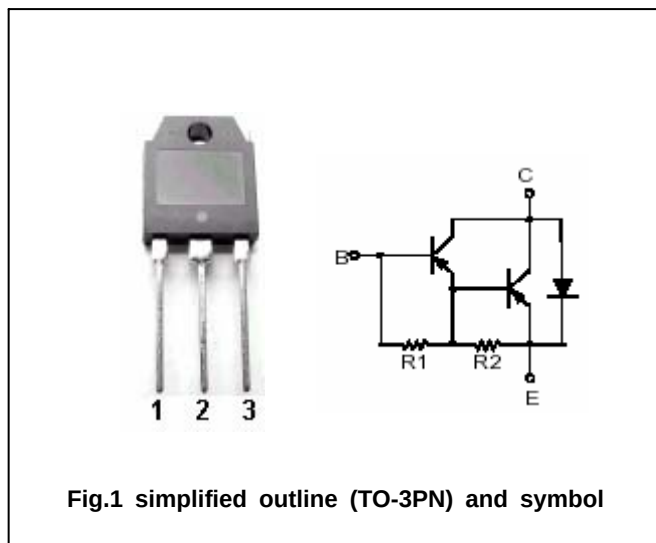
- With TO-3PN package
- High DC current gain.
- Large current capacity and wide ASO.
- Low saturation voltage.
- DARLINGTON

APPLICATIONS

- Motor drivers, printer
- Hammer drivers
- Relay drivers,
- Voltage regulator control

PINNING

PIN	DESCRIPTION
1	Base
2	Collector;connected to mounting base
3	Emitter

Absolute maximum ratings($T_c=25^\circ\text{C}$)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	-110	V
V_{CEO}	Collector-emitter voltage	Open base	-100	V
V_{EBO}	Emitter-base voltage	Open collector	-6	V
I_C	Collector current (DC)		-10	A
I_{CM}	Collector current-peak		-15	A
P_C	Collector power dissipation	$T_c=25^\circ\text{C}$	70	W
T_j	Junction temperature		150	$^\circ\text{C}$
T_{stg}	Storage temperature		-55~150	$^\circ\text{C}$

Silicon PNP Power Transistors

2SB887

CHARACTERISTICS

Tj=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-emitter breakdown voltage	$I_C = -50\text{mA}$; $R_{BE} = \infty$	-100			V
$V_{(BR)CBO}$	Collector-base breakdown voltage	$I_C = -5\text{mA}$; $I_E = 0$	-110			V
V_{CEsat}	Collector-emitter saturation voltage	$I_C = -5\text{A}$; $I_B = -10\text{mA}$		-1.0	-1.5	V
V_{BEsat}	Base-emitter saturation voltage	$I_C = -5\text{A}$; $I_B = -10\text{mA}$			-2.0	V
I_{CBO}	Collector cut-off current	$V_{CB} = -80\text{V}$; $I_E = 0$			-0.1	mA
I_{EBO}	Emitter cut-off current	$V_{EB} = -5\text{V}$; $I_C = 0$			-3.0	mA
h_{FE}	DC current gain	$I_C = -5\text{A}$; $V_{CE} = -3\text{V}$	1500	4000		
f_T	Transition frequency	$I_C = -5\text{A}$; $V_{CE} = -5\text{V}$		20		MHz

Silicon PNP Power Transistors

2SB887

PACKAGE OUTLINE

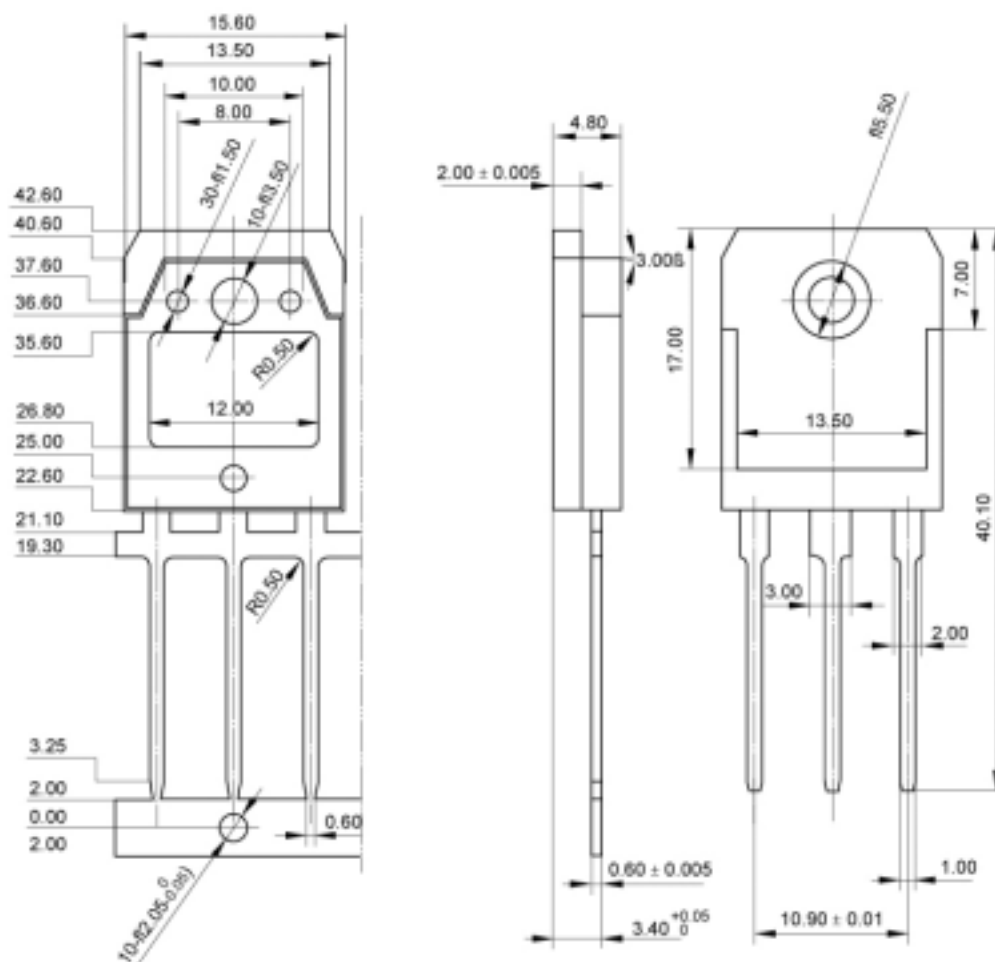


Fig.2 outline dimensions